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### Understanding **Embedded - FPGAs (Field Programmable Gate Array)**

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	55296
Number of I/O	178
Number of Gates	400000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (Tj)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/a3p400-1fg256">https://www.e-xfl.com/product-detail/microchip-technology/a3p400-1fg256</a>

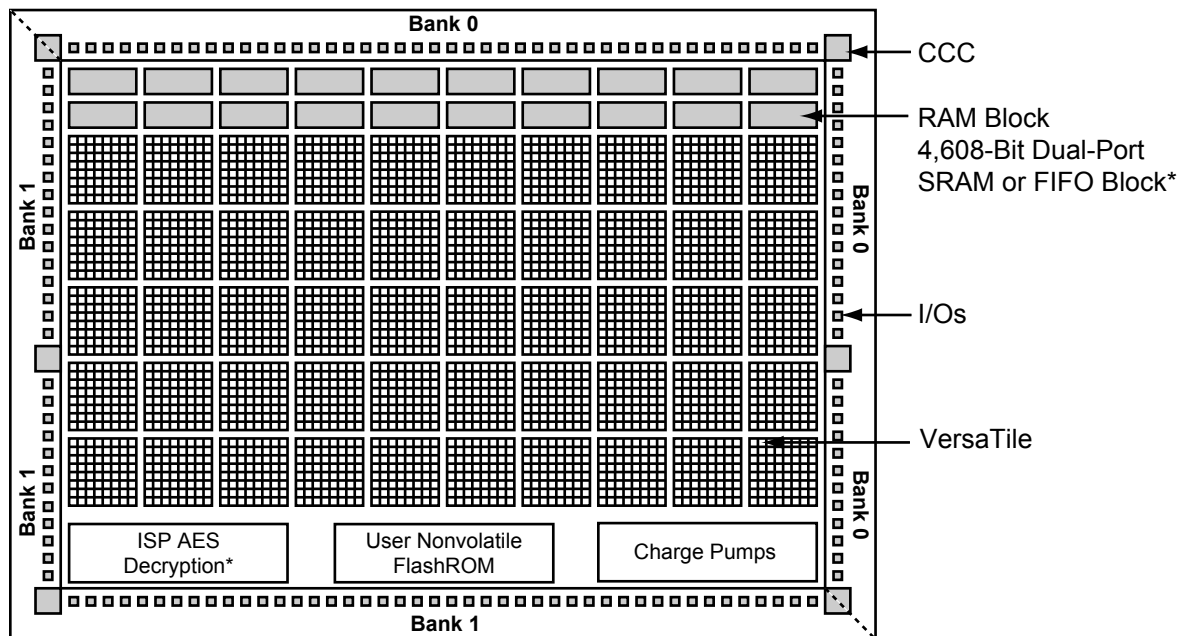
## Advanced Flash Technology

The ProASIC3 family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVC MOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

## Advanced Architecture

The proprietary ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory†
- Extensive CCCs and PLLs†
- Advanced I/O structure



*Note:* \*Not supported by A3P015 and A3P030 devices

**Figure 1-1 • ProASIC3 Device Architecture Overview with Two I/O Banks (A3P015, A3P030, A3P060, and A3P125)**

† The A3P015 and A3P030 do not support PLL or SRAM.

## 2 – ProASIC3 DC and Switching Characteristics

### General Specifications

#### Operating Conditions

Stresses beyond those listed in [Table 2-1](#) may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in [Table 2-2](#) on [page 2-2](#) is not implied.

**Table 2-1 • Absolute Maximum Ratings**

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O output buffer supply voltage	–0.3 to 3.75	V
VMV	DC I/O input buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)	V
T <sub>STG</sub> <sup>2</sup>	Storage temperature	–65 to +150	°C
T <sub>J</sub> <sup>2</sup>	Junction temperature	+125	°C

**Notes:**

1. The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in [Table 2-4](#) on [page 2-3](#).
2. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on [page 3-1](#) for further information.
3. For flash programming and retention maximum limits, refer to [Table 2-3](#) on [page 2-3](#), and for recommended operating limits, refer to [Table 2-2](#) on [page 2-2](#).

**Table 2-42 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 3.0\text{ V}$**   
**Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	10.26	0.04	1.02	0.43	10.45	8.90	2.64	2.46	12.68	11.13	ns
	-1	0.56	8.72	0.04	0.86	0.36	8.89	7.57	2.25	2.09	10.79	9.47	ns
	-2	0.49	7.66	0.03	0.76	0.32	7.80	6.64	1.98	1.83	9.47	8.31	ns
4 mA	Std.	0.66	10.26	0.04	1.02	0.43	10.45	8.90	2.64	2.46	12.68	11.13	ns
	-1	0.56	8.72	0.04	0.86	0.36	8.89	7.57	2.25	2.09	10.79	9.47	ns
	-2	0.49	7.66	0.03	0.76	0.32	7.80	6.64	1.98	1.83	9.47	8.31	ns
6 mA	Std.	0.66	7.27	0.04	1.02	0.43	7.41	6.28	2.98	3.04	9.65	8.52	ns
	-1	0.56	6.19	0.04	0.86	0.36	6.30	5.35	2.54	2.59	8.20	7.25	ns
	-2	0.49	5.43	0.03	0.76	0.32	5.53	4.69	2.23	2.27	7.20	6.36	ns
8 mA	Std.	0.66	7.27	0.04	1.02	0.43	7.41	6.28	2.98	3.04	9.65	8.52	ns
	-1	0.56	6.19	0.04	0.86	0.36	6.30	5.35	2.54	2.59	8.20	7.25	ns
	-2	0.49	5.43	0.03	0.76	0.32	5.53	4.69	2.23	2.27	7.20	6.36	ns
12 mA	Std.	0.66	5.58	0.04	1.02	0.43	5.68	4.87	3.21	3.42	7.92	7.11	ns
	-1	0.56	4.75	0.04	0.86	0.36	4.84	4.14	2.73	2.91	6.74	6.05	ns
	-2	0.49	4.17	0.03	0.76	0.32	4.24	3.64	2.39	2.55	5.91	5.31	ns
16 mA	Std.	0.66	5.21	0.04	1.02	0.43	5.30	4.56	3.26	3.51	7.54	6.80	ns
	-1	0.56	4.43	0.04	0.86	0.36	4.51	3.88	2.77	2.99	6.41	5.79	ns
	-2	0.49	3.89	0.03	0.76	0.32	3.96	3.41	2.43	2.62	5.63	5.08	ns
24 mA	Std.	0.66	4.85	0.04	1.02	0.43	4.94	4.54	3.32	3.88	7.18	6.78	ns
	-1	0.56	4.13	0.04	0.86	0.36	4.20	3.87	2.82	3.30	6.10	5.77	ns
	-2	0.49	3.62	0.03	0.76	0.32	3.69	3.39	2.48	2.90	5.36	5.06	ns

*Note:* For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-53 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V**  
**Applicable to Standard Plus I/O Banks**

Drive Strength	Equiv. Software Default Drive Strength Option <sup>1</sup>	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
100 $\mu\text{A}$	2 mA	Std.	0.60	14.97	0.04	1.52	0.43	14.97	12.79	3.52	3.41	18.36	16.18	ns
		-1	0.51	12.73	0.04	1.29	0.36	12.73	10.88	2.99	2.90	15.62	13.77	ns
		-2	0.45	11.18	0.03	1.14	0.32	11.18	9.55	2.63	2.55	13.71	12.08	ns
100 $\mu\text{A}$	4 mA	Std.	0.60	10.36	0.04	1.52	0.43	10.36	8.93	3.99	4.24	13.75	12.33	ns
		-1	0.51	8.81	0.04	1.29	0.36	8.81	7.60	3.39	3.60	11.70	10.49	ns
		-2	0.45	7.74	0.03	1.14	0.32	7.74	6.67	2.98	3.16	10.27	9.21	ns
100 $\mu\text{A}$	6 mA	Std.	0.60	10.36	0.04	1.52	0.43	10.36	8.93	3.99	4.24	13.75	12.33	ns
		-1	0.51	8.81	0.04	1.29	0.36	8.81	7.60	3.39	3.60	11.70	10.49	ns
		-2	0.45	7.74	0.03	1.14	0.32	7.74	6.67	2.98	3.16	10.27	9.21	ns
100 $\mu\text{A}$	8 mA	Std.	0.60	7.81	0.04	1.52	0.43	7.81	6.85	4.32	4.76	11.20	10.24	ns
		-1	0.51	6.64	0.04	1.29	0.36	6.64	5.82	3.67	4.05	9.53	8.71	ns
		-2	0.45	5.83	0.03	1.14	0.32	5.83	5.11	3.22	3.56	8.36	7.65	ns
100 $\mu\text{A}$	16 mA	Std.	0.60	7.81	0.04	1.52	0.43	7.81	6.85	4.32	4.76	11.20	10.24	ns
		-1	0.51	6.64	0.04	1.29	0.36	6.64	5.82	3.67	4.05	9.53	8.71	ns
		-2	0.45	5.83	0.03	1.14	0.32	5.83	5.11	3.22	3.56	8.36	7.65	ns

**Notes:**

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100 \mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-55 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V**  
**Applicable to Standard I/O Banks**

Drive Strength	Equiv. Software Default Drive Strength Option <sup>1</sup>	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
100 $\mu\text{A}$	2 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		-1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		-2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 $\mu\text{A}$	4 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		-1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		-2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 $\mu\text{A}$	6 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		-1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		-2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns
100 $\mu\text{A}$	8 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		-1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		-2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns

**Notes:**

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100 \mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-62 • 2.5 V LVC MOS High Slew**  
 Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 2.3\text{ V}$   
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
4 mA	Std.	0.66	8.28	0.04	1.30	0.43	7.41	8.28	2.25	2.07	9.64	10.51	ns
	-1	0.56	7.04	0.04	1.10	0.36	6.30	7.04	1.92	1.76	8.20	8.94	ns
	-2	0.49	6.18	0.03	0.97	0.32	5.53	6.18	1.68	1.55	7.20	7.85	ns
6 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	-1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	-2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
8 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	-1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	-2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
12 mA	Std.	0.66	3.21	0.04	1.30	0.43	3.27	3.14	2.82	3.11	5.50	5.38	ns
	-1	0.56	2.73	0.04	1.10	0.36	2.78	2.67	2.40	2.65	4.68	4.57	ns
	-2	0.49	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns

## Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-63 • 2.5 V LVC MOS Low Slew**  
 Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 2.3\text{ V}$   
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
4 mA	Std.	0.66	10.84	0.04	1.30	0.43	10.64	10.84	2.26	1.99	12.87	13.08	ns
	-1	0.56	9.22	0.04	1.10	0.36	9.05	9.22	1.92	1.69	10.95	11.12	ns
	-2	0.49	8.10	0.03	0.97	0.32	7.94	8.10	1.68	1.49	9.61	9.77	ns
6 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	-1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	-2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
8 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	-1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	-2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
12 mA	Std.	0.66	5.63	0.04	1.30	0.43	5.73	5.51	2.83	3.01	7.97	7.74	ns
	-1	0.56	4.79	0.04	1.10	0.36	4.88	4.68	2.41	2.56	6.78	6.59	ns
	-2	0.49	4.20	0.03	0.97	0.32	4.28	4.11	2.11	2.25	5.95	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-73 • 1.8 V LVC MOS Low Slew**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V  
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	14.80	0.04	1.20	0.43	13.49	14.80	2.25	1.46	15.73	17.04	ns
	-1	0.56	12.59	0.04	1.02	0.36	11.48	12.59	1.91	1.25	13.38	14.49	ns
	-2	0.49	11.05	0.03	0.90	0.32	10.08	11.05	1.68	1.09	11.75	12.72	ns
4 mA	Std.	0.66	9.90	0.04	1.20	0.43	9.73	9.90	2.65	2.50	11.97	12.13	ns
	-1	0.56	8.42	0.04	1.02	0.36	8.28	8.42	2.26	2.12	10.18	10.32	ns
	-2	0.49	7.39	0.03	0.90	0.32	7.27	7.39	1.98	1.86	8.94	9.06	ns
6 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	-1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	-2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns
8 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	-1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	-2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

**Table 2-74 • 1.8 V LVC MOS High Slew**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V  
 Applicable to Standard I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	-1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	-2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	-1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	-2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



## Timing Characteristics

**Table 2-80 • 1.5 V LVC MOS High Slew**

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 1.4\text{ V}$   
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	0.66	8.36	0.04	1.44	0.43	6.82	8.36	3.39	2.77	9.06	10.60	ns
	-1	0.56	7.11	0.04	1.22	0.36	5.80	7.11	2.88	2.35	7.71	9.02	ns
	-2	0.49	6.24	0.03	1.07	0.32	5.10	6.24	2.53	2.06	6.76	7.91	ns
4 mA	Std.	0.66	5.31	0.04	1.44	0.43	4.85	5.31	3.74	3.40	7.09	7.55	ns
	-1	0.56	4.52	0.04	1.22	0.36	4.13	4.52	3.18	2.89	6.03	6.42	ns
	-2	0.49	3.97	0.03	1.07	0.32	3.62	3.97	2.79	2.54	5.29	5.64	ns
6 mA	Std.	0.66	4.67	0.04	1.44	0.43	4.55	4.67	3.82	3.56	6.78	6.90	ns
	-1	0.56	3.97	0.04	1.22	0.36	3.87	3.97	3.25	3.03	5.77	5.87	ns
	-2	0.49	3.49	0.03	1.07	0.32	3.40	3.49	2.85	2.66	5.07	5.16	ns
8 mA	Std.	0.66	4.08	0.04	1.44	0.43	4.15	3.58	3.94	4.20	6.39	5.81	ns
	-1	0.56	3.47	0.04	1.22	0.36	3.53	3.04	3.36	3.58	5.44	4.95	ns
	-2	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns
12 mA	Std.	0.66	4.08	0.04	1.44	0.43	4.15	3.58	3.94	4.20	6.39	5.81	ns
	-1	0.56	3.47	0.04	1.22	0.36	3.53	3.04	3.36	3.58	5.44	4.95	ns
	-2	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns

### Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-97 • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
$t_{OCLKQ}$	Clock-to-Q of the Output Data Register	HH, DOUT
$t_{OSUD}$	Data Setup Time for the Output Data Register	FF, HH
$t_{OHD}$	Data Hold Time for the Output Data Register	FF, HH
$t_{OSUE}$	Enable Setup Time for the Output Data Register	GG, HH
$t_{OHE}$	Enable Hold Time for the Output Data Register	GG, HH
$t_{OCLR2Q}$	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OEMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
$t_{OECLKQ}$	Clock-to-Q of the Output Enable Register	HH, EOUT
$t_{OESUD}$	Data Setup Time for the Output Enable Register	JJ, HH
$t_{OEHD}$	Data Hold Time for the Output Enable Register	JJ, HH
$t_{OESUE}$	Enable Setup Time for the Output Enable Register	KK, HH
$t_{OEHE}$	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
$t_{ICLKQ}$	Clock-to-Q of the Input Data Register	AA, EE
$t_{ISUD}$	Data Setup Time for the Input Data Register	CC, AA
$t_{IHD}$	Data Hold Time for the Input Data Register	CC, AA
$t_{ISUE}$	Enable Setup Time for the Input Data Register	BB, AA
$t_{IHE}$	Enable Hold Time for the Input Data Register	BB, AA
$t_{ICLR2Q}$	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note:* \*See Figure 2-16 on page 2-71 for more information.

## Embedded SRAM and FIFO Characteristics

### SRAM

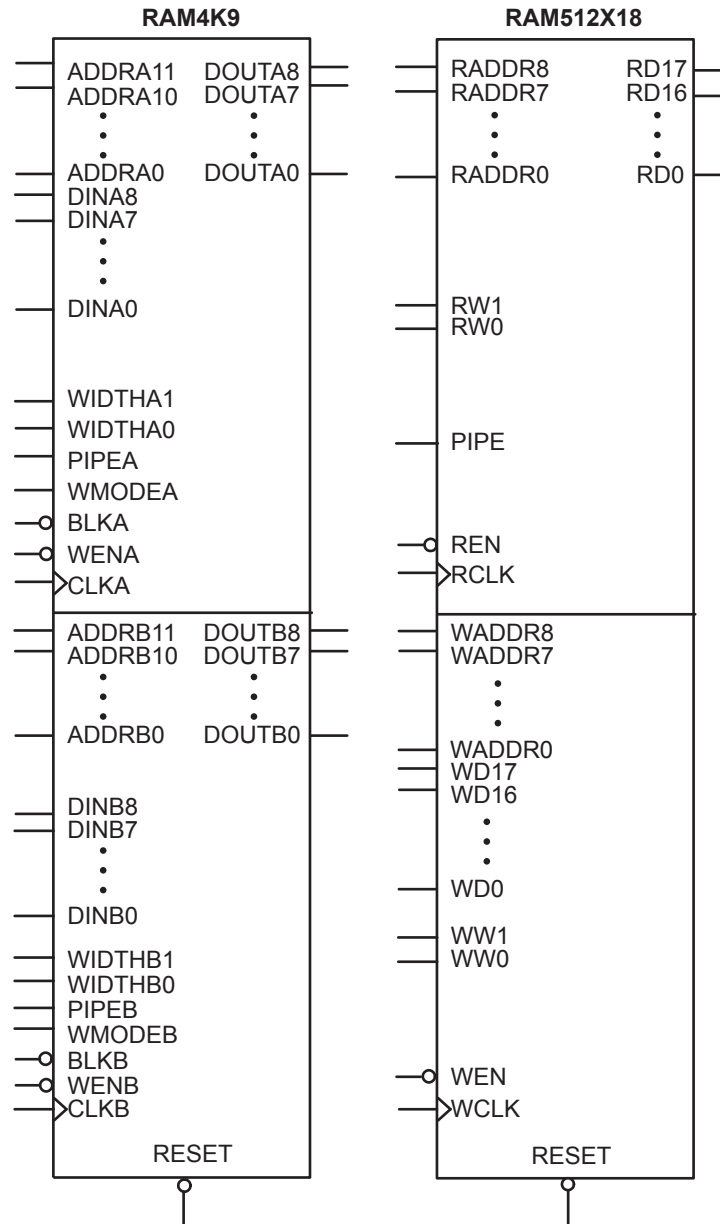


Figure 2-30 • RAM Models

## Timing Characteristics

**Table 2-116 • RAM4K9**

 Commercial-Case Conditions:  $T_j = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ 

Parameter	Description	-2	-1	Std.	Units
$t_{AS}$	Address setup time	0.25	0.28	0.33	ns
$t_{AH}$	Address hold time	0.00	0.00	0.00	ns
$t_{ENS}$	REN, WEN setup time	0.14	0.16	0.19	ns
$t_{ENH}$	REN, WEN hold time	0.10	0.11	0.13	ns
$t_{BKS}$	BLK setup time	0.23	0.27	0.31	ns
$t_{BKH}$	BLK hold time	0.02	0.02	0.02	ns
$t_{DS}$	Input data (DIN) setup time	0.18	0.21	0.25	ns
$t_{DH}$	Input data (DIN) hold time	0.00	0.00	0.00	ns
$t_{CKQ1}$	Clock High to new data valid on DOUT (output retained, WMODE = 0)	2.36	2.68	3.15	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	1.79	2.03	2.39	ns
$t_{CKQ2}$	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
$t_{C2CWWL}^1$	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
$t_{C2CWWH}^1$	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
$t_{C2CRWH}^1$	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
$t_{C2CWRH}^1$	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.49	0.42	0.37	ns
$t_{RSTBQ}$	RESET Low to data out Low on DOUT (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DOUT (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
$t_{CYC}$	Clock cycle time	3.23	3.68	4.32	ns
$F_{MAX}$	Maximum frequency	310	272	231	MHz

### Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-122 • A3P250 FIFO 2k×2**  
**Worst Commercial-Case Conditions: T<sub>J</sub> = 70°C, VCC = 1.425 V**

Parameter	Description	-2	-1	Std.	Units
t <sub>ENS</sub>	REN, WEN Setup Time	4.39	5.00	5.88	ns
t <sub>ENH</sub>	REN, WEN Hold Time	0.00	0.00	0.00	ns
t <sub>BKS</sub>	BLK Setup Time	0.19	0.22	0.26	ns
t <sub>BKH</sub>	BLK Hold Time	0.00	0.00	0.00	ns
t <sub>DS</sub>	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t <sub>DH</sub>	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t <sub>CKQ1</sub>	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t <sub>CKQ2</sub>	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t <sub>RCKEF</sub>	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t <sub>WCKFF</sub>	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t <sub>CKAF</sub>	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t <sub>RSTFG</sub>	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t <sub>RSTAF</sub>	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t <sub>RSTBQ</sub>	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
t <sub>REMRSTB</sub>	RESET Removal	0.29	0.33	0.38	ns
t <sub>RECRSTB</sub>	RESET Recovery	1.50	1.71	2.01	ns
t <sub>MPWRSTB</sub>	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t <sub>CYC</sub>	Clock Cycle Time	3.23	3.68	4.32	ns
F <sub>MAX</sub>	Maximum Frequency for FIFO	310	272	231	MHz

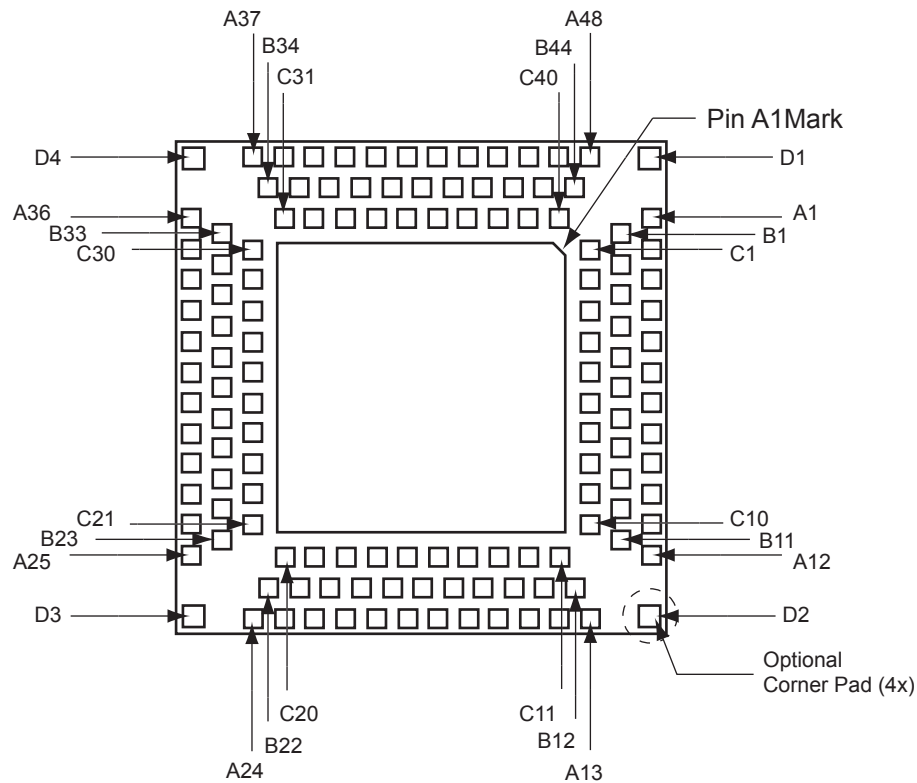
**Table 2-123 • A3P250 FIFO 4k×1**  
**Worst Commercial-Case Conditions: T<sub>J</sub> = 70°C, VCC = 1.425 V**

Parameter	Description	-2	-1	Std.	Units
t <sub>ENS</sub>	REN, WEN Setup Time	4.86	5.53	6.50	ns
t <sub>ENH</sub>	REN, WEN Hold Time	0.00	0.00	0.00	ns
t <sub>BKS</sub>	BLK Setup Time	0.19	0.22	0.26	ns
t <sub>BKH</sub>	BLK Hold Time	0.00	0.00	0.00	ns
t <sub>DS</sub>	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t <sub>DH</sub>	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t <sub>CKQ1</sub>	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t <sub>CKQ2</sub>	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t <sub>RCKEF</sub>	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t <sub>WCKFF</sub>	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t <sub>CKAF</sub>	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t <sub>RSTFG</sub>	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns

QN68	
Pin Number	A3P030 Function
1	IO82RSB1
2	IO80RSB1
3	IO78RSB1
4	IO76RSB1
5	GEC0/IO73RSB1
6	GEA0/IO72RSB1
7	GEB0/IO71RSB1
8	VCC
9	GND
10	VCCIB1
11	IO68RSB1
12	IO67RSB1
13	IO66RSB1
14	IO65RSB1
15	IO64RSB1
16	IO63RSB1
17	IO62RSB1
18	IO60RSB1
19	IO58RSB1
20	IO56RSB1
21	IO54RSB1
22	IO52RSB1
23	IO51RSB1
24	VCC
25	GND
26	VCCIB1
27	IO50RSB1
28	IO48RSB1
29	IO46RSB1
30	IO44RSB1
31	IO42RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP
36	TDO

QN68	
Pin Number	A3P030 Function
37	TRST
38	VJTAG
39	IO40RSB0
40	IO37RSB0
41	GDB0/IO34RSB0
42	GDA0/IO33RSB0
43	GDC0/IO32RSB0
44	VCCIB0
45	GND
46	VCC
47	IO31RSB0
48	IO29RSB0
49	IO28RSB0
50	IO27RSB0
51	IO25RSB0
52	IO24RSB0
53	IO22RSB0
54	IO21RSB0
55	IO19RSB0
56	IO17RSB0
57	IO15RSB0
58	IO14RSB0
59	VCCIB0
60	GND
61	VCC
62	IO12RSB0
63	IO10RSB0
64	IO08RSB0
65	IO06RSB0
66	IO04RSB0
67	IO02RSB0
68	IO00RSB0

## QN132 – Bottom View



### Notes:

1. The die attach paddle center of the package is tied to ground (GND).
2. Option corner pads come with this device and package combination. It is optional to tie them to ground or leave them floating.
3. The QN132 package is discontinued and is not available for ProASIC3 devices.
4. For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

TQ144	
Pin Number	A3P125 Function
1	GAA2/IO67RSB1
2	IO68RSB1
3	GAB2/IO69RSB1
4	IO132RSB1
5	GAC2/IO131RSB1
6	IO130RSB1
7	IO129RSB1
8	IO128RSB1
9	VCC
10	GND
11	VCCIB1
12	IO127RSB1
13	GFC1/IO126RSB1
14	GFC0/IO125RSB1
15	GFB1/IO124RSB1
16	GFB0/IO123RSB1
17	VCOMPLF
18	GFA0/IO122RSB1
19	VCCPLF
20	GFA1/IO121RSB1
21	GFA2/IO120RSB1
22	GFB2/IO119RSB1
23	GFC2/IO118RSB1
24	IO117RSB1
25	IO116RSB1
26	IO115RSB1
27	GND
28	VCCIB1
29	GEC1/IO112RSB1
30	GEC0/IO111RSB1
31	GEB1/IO110RSB1
32	GEB0/IO109RSB1
33	GEA1/IO108RSB1
34	GEA0/IO107RSB1
35	VMV1
36	GNDQ

TQ144	
Pin Number	A3P125 Function
37	NC
38	GEA2/IO106RSB1
39	GEB2/IO105RSB1
40	GEC2/IO104RSB1
41	IO103RSB1
42	IO102RSB1
43	IO101RSB1
44	IO100RSB1
45	VCC
46	GND
47	VCCIB1
48	IO99RSB1
49	IO97RSB1
50	IO95RSB1
51	IO93RSB1
52	IO92RSB1
53	IO90RSB1
54	IO88RSB1
55	IO86RSB1
56	IO84RSB1
57	IO83RSB1
58	IO82RSB1
59	IO81RSB1
60	IO80RSB1
61	IO79RSB1
62	VCC
63	GND
64	VCCIB1
65	GDC2/IO72RSB1
66	GDB2/IO71RSB1
67	GDA2/IO70RSB1
68	GNDQ
69	TCK
70	TDI
71	TMS
72	VMV1

TQ144	
Pin Number	A3P125 Function
73	VPUMP
74	NC
75	TDO
76	TRST
77	VJTAG
78	GDA0/IO66RSB0
79	GDB0/IO64RSB0
80	GDB1/IO63RSB0
81	VCCIB0
82	GND
83	IO60RSB0
84	GCC2/IO59RSB0
85	GCB2/IO58RSB0
86	GCA2/IO57RSB0
87	GCA0/IO56RSB0
88	GCA1/IO55RSB0
89	GCB0/IO54RSB0
90	GCB1/IO53RSB0
91	GCC0/IO52RSB0
92	GCC1/IO51RSB0
93	IO50RSB0
94	IO49RSB0
95	NC
96	NC
97	NC
98	VCCIB0
99	GND
100	VCC
101	IO47RSB0
102	GBC2/IO45RSB0
103	IO44RSB0
104	GBB2/IO43RSB0
105	IO42RSB0
106	GBA2/IO41RSB0
107	VMV0
108	GNDQ



FG256	
Pin Number	A3P250 Function
G13	GCC1/IO48PPB1
G14	IO47NPB1
G15	IO54PDB1
G16	IO54NDB1
H1	GFB0/IO109NPB3
H2	GFA0/IO108NDB3
H3	GFB1/IO109PPB3
H4	VCOMPLF
H5	GFC0/IO110NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO48NPB1
H13	GCB1/IO49PPB1
H14	GCA0/IO50NPB1
H15	NC
H16	GCB0/IO49NPB1
J1	GFA2/IO107PPB3
J2	GFA1/IO108PDB3
J3	VCCPLF
J4	IO106NDB3
J5	GFB2/IO106PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO52PPB1
J13	GCA1/IO50PPB1
J14	GCC2/IO53PPB1
J15	NC
J16	GCA2/IO51PDB1

FG256	
Pin Number	A3P250 Function
K1	GFC2/IO105PDB3
K2	IO107NPB3
K3	IO104PPB3
K4	NC
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO52NPB1
K14	IO55RSB1
K15	IO53NPB1
K16	IO51NDB1
L1	IO105NDB3
L2	IO104NPB3
L3	NC
L4	IO102RSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO59VPB1
L14	IO57VDB1
L15	IO57UDB1
L16	IO56PDB1
M1	IO103PDB3
M2	NC
M3	IO101NPB3
M4	GEC0/IO100NPB3

FG256	
Pin Number	A3P250 Function
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	NC
M9	IO74RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	NC
M14	GDB1/IO59UPB1
M15	GDC1/IO58UDB1
M16	IO56NDB1
N1	IO103NDB3
N2	IO101PPB3
N3	GEC1/IO100PPB3
N4	NC
N5	GNDQ
N6	GEA2/IO97RSB2
N7	IO86RSB2
N8	IO82RSB2
N9	IO75RSB2
N10	IO69RSB2
N11	IO64RSB2
N12	GNDQ
N13	NC
N14	VJTAG
N15	GDC0/IO58VDB1
N16	GDA1/IO60UDB1
P1	GEB1/IO99PDB3
P2	GEB0/IO99NDB3
P3	NC
P4	NC
P5	IO92RSB2
P6	IO89RSB2
P7	IO85RSB2
P8	IO81RSB2

FG256	
Pin Number	A3P250 Function
P9	IO76RSB2
P10	IO71RSB2
P11	IO66RSB2
P12	NC
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO60VDB1
R1	GEA1/IO98PDB3
R2	GEA0/IO98NDB3
R3	NC
R4	GEC2/IO95RSB2
R5	IO91RSB2
R6	IO88RSB2
R7	IO84RSB2
R8	IO80RSB2
R9	IO77RSB2
R10	IO72RSB2
R11	IO68RSB2
R12	IO65RSB2
R13	GDB2/IO62RSB2
R14	TDI
R15	NC
R16	TDO
T1	GND
T2	IO94RSB2
T3	GEB2/IO96RSB2
T4	IO93RSB2
T5	IO90RSB2
T6	IO87RSB2
T7	IO83RSB2
T8	IO79RSB2
T9	IO78RSB2
T10	IO73RSB2
T11	IO70RSB2
T12	GDC2/IO63RSB2

FG256	
Pin Number	A3P250 Function
T13	IO67RSB2
T14	GDA2/IO61RSB2
T15	TMS
T16	GND

FG484	
Pin Number	A3P400 Function
E21	NC
E22	NC
F1	NC
F2	NC
F3	NC
F4	IO154VDB3
F5	IO155VDB3
F6	IO11RSB0
F7	IO07RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO20RSB0
F11	IO24RSB0
F12	IO33RSB0
F13	IO39RSB0
F14	IO45RSB0
F15	GBC0/IO54RSB0
F16	IO48RSB0
F17	VMV0
F18	IO61NPB1
F19	IO63PDB1
F20	NC
F21	NC
F22	NC
G1	NC
G2	NC
G3	NC
G4	IO151VDB3
G5	IO151UDB3
G6	GAC2/IO153UDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0

FG484	
Pin Number	A3P400 Function
G13	IO40RSB0
G14	IO46RSB0
G15	GNDQ
G16	IO47RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO150PDB3
H5	IO08RSB0
H6	IO153VDB3
H7	IO152VDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO65RSB1
H18	IO52RSB0
H19	IO66PDB1
H20	VCC
H21	NC
H22	NC
J1	NC
J2	NC
J3	NC
J4	IO150NDB3

FG484	
Pin Number	A3P400 Function
J5	IO149NPB3
J6	IO09RSB0
J7	IO152UDB3
J8	VCCIB3
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB1
J16	IO62NDB1
J17	IO49RSB0
J18	IO64PPB1
J19	IO66NDB1
J20	NC
J21	NC
J22	NC
K1	NC
K2	NC
K3	NC
K4	IO148NDB3
K5	IO148PDB3
K6	IO149PPB3
K7	GFC1/IO147PPB3
K8	VCCIB3
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO67PPB1
K17	IO64NPB1
K18	IO73PDB1

Revision	Changes	Page
v2.0 (continued)	Table 3-20 • Summary of I/O Timing Characteristics—Software Default Settings (Advanced) and Table 3-21 • Summary of I/O Timing Characteristics—Software Default Settings (Standard Plus) were updated.	3-20 to 3-20
	Table 3-11 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices was updated.	3-9
	Table 3-24 • I/O Output Buffer Maximum Resistances1 (Advanced) and Table 3-25 • I/O Output Buffer Maximum Resistances1 (Standard Plus) were updated.	3-22 to 3-22
	Table 3-17 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions was updated.	3-18
	Table 3-28 • I/O Short Currents IOSH/IOSL (Advanced) and Table 3-29 • I/O Short Currents IOSH/IOSL (Standard Plus) were updated.	3-24 to 3-26
	The note in Table 3-32 • I/O Input Rise Time, Fall Time, and Related I/O Reliability was updated.	3-27
	Figure 3-33 • Write Access After Write onto Same Address, Figure 3-34 • Read Access After Write onto Same Address, and Figure 3-35 • Write Access After Read onto Same Address are new.	3-82 to 3-84
	Figure 3-43 • Timing Diagram was updated.	3-96
	Ambient was deleted from the "Speed Grade and Temperature Grade Matrix".	iv
	Notes were added to the package diagrams identifying if they were top or bottom view.	N/A
	The A3P030 "132-Pin QFN" table is new.	4-2
	The A3P060 "132-Pin QFN" table is new.	4-4
	The A3P125 "132-Pin QFN" table is new.	4-6
	The A3P250 "132-Pin QFN" table is new.	4-8
The A3P030 "100-Pin VQFP" table is new.	4-11	
Advance v0.7 (January 2007)	In the "I/Os Per Package" table, the I/O numbers were added for A3P060, A3P125, and A3P250. The A3P030-VQ100 I/O was changed from 79 to 77.	ii
Advance v0.6 (April 2006)	The term flow-through was changed to pass-through.	N/A
	Table 1 was updated to include the QN132.	ii
	The "I/Os Per Package" table was updated with the QN132. The footnotes were also updated. The A3P400-FG144 I/O count was updated.	ii
	"Automotive ProASIC3 Ordering Information" was updated with the QN132.	iii
	"Temperature Grade Offerings" was updated with the QN132.	iii
	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-7 • Efficient Long-Line Resources was updated.	2-7
	The footnotes in Figure 2-15 • Clock Input Sources Including CLKBUF, CLKBUF_LVDS/LVPECL, and CLKINT were updated.	2-16
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
The "SRAM and FIFO" section was updated.	2-21	

## Datasheet Categories

### **Categories**

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "ProASIC3 Device Status" table on page IV, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

#### **Product Brief**

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

#### **Advance**

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

#### **Preliminary**

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

#### **Unmarked (production)**

This version contains information that is considered to be final.

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